

FDMA520PZ

Single P-Channel PowerTrench® MOSFET

-20V, -7.3A, 30mΩ

Features

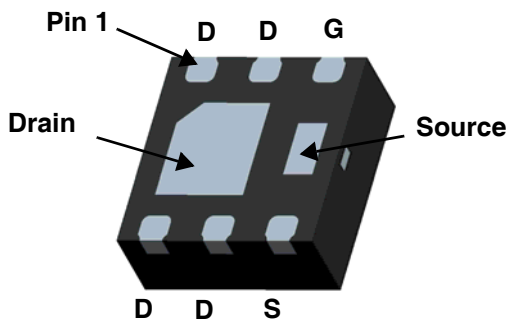
- Max $r_{DS(on)}$ = 30mΩ at $V_{GS} = -4.5V$, $I_D = -7.3A$
- Max $r_{DS(on)}$ = 53mΩ at $V_{GS} = -2.5V$, $I_D = -5.5A$
- Low profile - 0.8mm maximum - in the new package MicroFET 2X2 mm
- RoHS Compliant



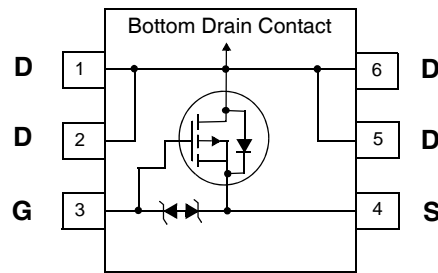
General Description

This device is designed specifically for battery charge or load switching in cellular handset and other ultraportable applications. It features a MOSFET with low on-state resistance.

The MicroFET 2X2 package offers exceptional thermal performance for its physical size and is well suited to linear mode applications.



MicroFET 2X2 (Bottom View)



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	-20	V
V_{GS}	Gate to Source Voltage	±12	V
I_D	Drain Current -Continuous (Note 1a)	-7.3	A
	-Pulsed	-24	
P_D	Power Dissipation (Note 1a)	2.4	W
	Power Dissipation (Note 1b)	0.9	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	52	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1b)	145	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
520	FDMA520PZ	MicroFET 2X2	7"	8mm	3000 units

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = -250\mu\text{A}, V_{GS} = 0\text{V}$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\mu\text{A}$, referenced to 25°C		-8.4		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16\text{V}, V_{GS} = 0\text{V}$			-1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 12\text{V}, V_{DS} = 0\text{V}$			± 10	μA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = -250\mu\text{A}$	-0.6	-1.1	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = -250\mu\text{A}$, referenced to 25°C		3.5		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = -4.5\text{V}, I_D = -7.3\text{A}$		26	30	m Ω
		$V_{GS} = -2.5\text{V}, I_D = -5.5\text{A}$		42	53	
		$V_{GS} = -4.5\text{V}, I_D = -7.3\text{A}, T_J = 125^\circ\text{C}$		36	55	
g_{FS}	Forward Transconductance	$V_{DS} = -5\text{V}, I_D = -7.3\text{A}$		22		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = -10\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$		1235	1645	pF
C_{oss}	Output Capacitance			255	340	pF
C_{rss}	Reverse Transfer Capacitance			225	340	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -10\text{V}, I_D = -7.3\text{A}, V_{GS} = -4.5\text{V}, R_{GEN} = 6\Omega$		10	20	ns
t_r	Rise Time			29	47	ns
$t_{d(off)}$	Turn-Off Delay Time			83	133	ns
t_f	Fall Time			74	119	ns
Q_g	Total Gate Charge	$V_{DD} = -5\text{V}, I_D = -7.3\text{A}, V_{GS} = -4.5\text{V}$		14	20	nC
Q_{gs}	Gate to Source Gate Charge			2.9		nC
Q_{gd}	Gate to Drain "Miller" Charge			4.4		nC

Drain-Source Diode Characteristics

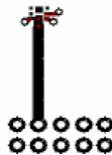
I_S	Maximum Continuous Drain-Source Diode Forward Current				-2	A
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = -2\text{A}$		-0.8	-1.2	V
t_{rr}	Reverse Recovery Time	$I_F = -7.3\text{A}, di/dt = 100\text{A}/\mu\text{s}$		30	45	ns
Q_{rr}	Reverse Recovery Charge			22	33	nC

Notes:

1: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.



a. $52^\circ\text{C}/\text{W}$ when mounted on a 1 in^2 pad of 2 oz copper



b. $145^\circ\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper

2: Pulse Test: Pulse Width < $300\mu\text{s}$, Duty cycle < 2.0%.

3: The diode connected between the gate and the source serves only as protection against ESD. No gate overvoltage rating is implied.

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

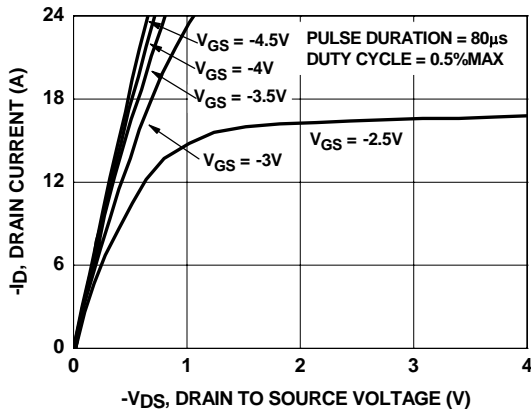


Figure 1. On-Region Characteristics

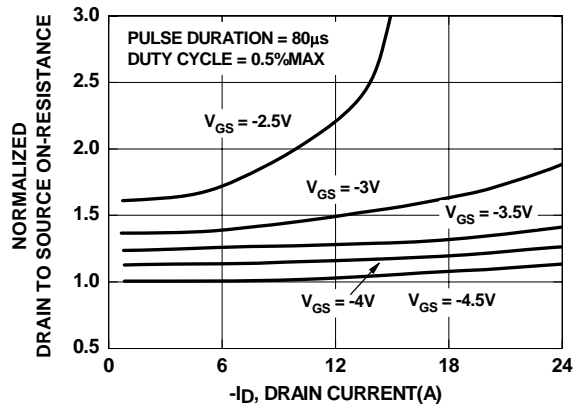


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

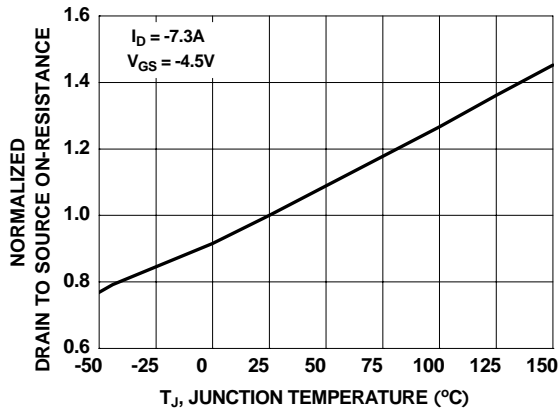


Figure 3. Normalized On-Resistance vs Junction Temperature

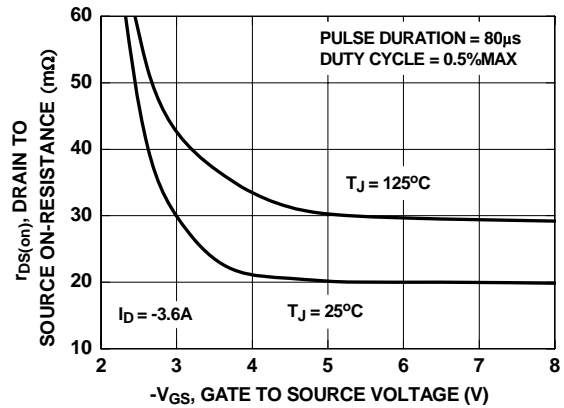


Figure 4. On-Resistance vs Gate to Source Voltage

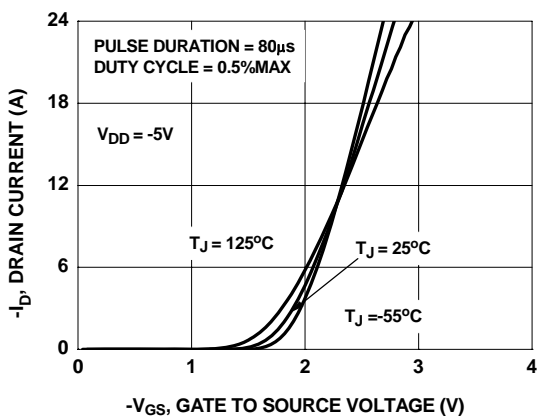


Figure 5. Transfer Characteristics

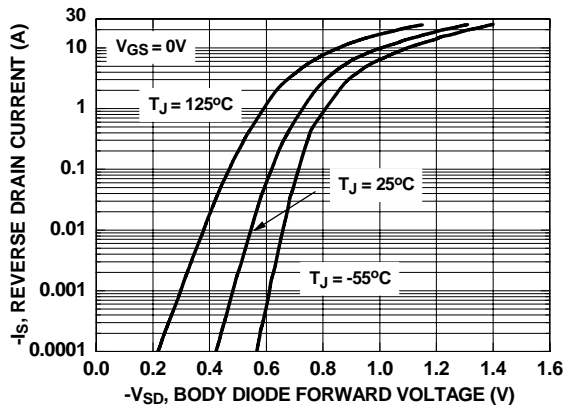


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

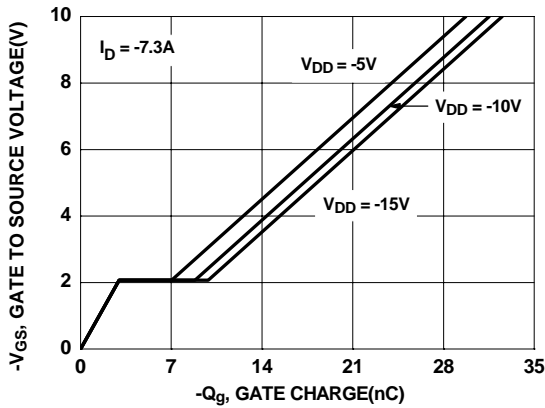


Figure 7. Gate Charge Characteristics

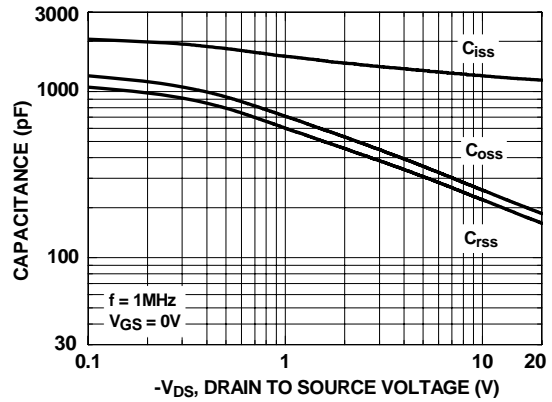


Figure 8. Capacitance vs Drain to Source Voltage

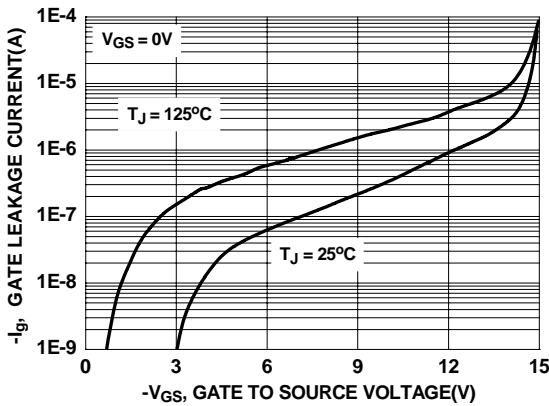


Figure 9. Gate Leakage Current vs Gate to Source Voltage

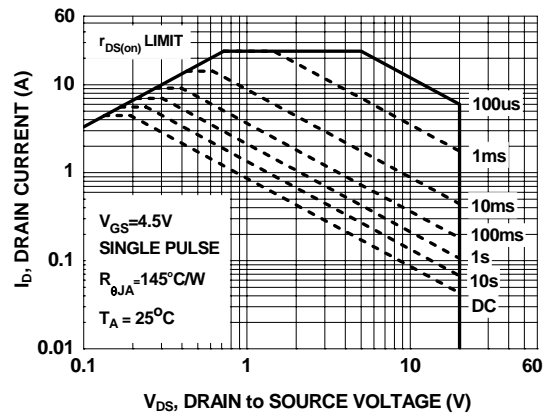


Figure 10. Forward Bias Safe Operating Area

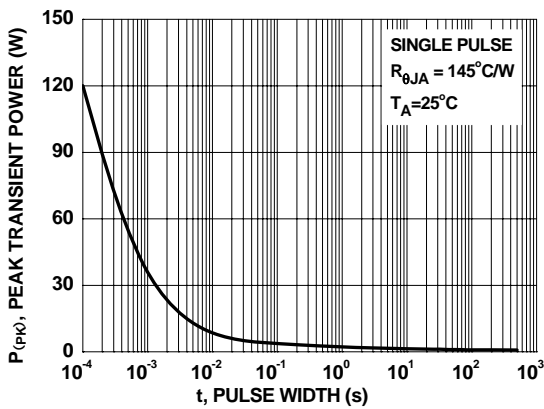


Figure 11. Single Pulse Maximum Power Dissipation

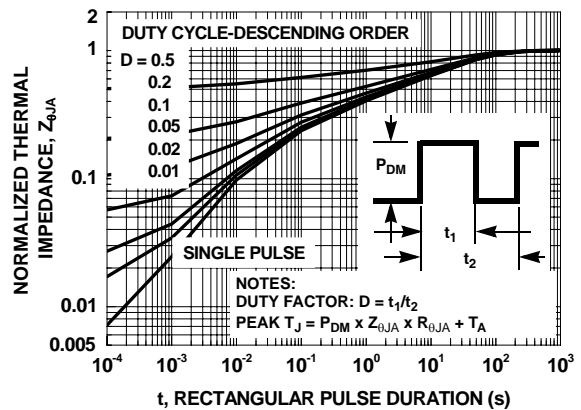


Figure 12. Transient Thermal Response Curve

